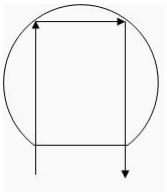
| Part Number | Customer |
|---|---|

| Category | | Parameter | Specification | Measurement Method |
|---|---|---|---|---|
| OverallWafer | 1.0 | Diameter | 150.00 +/- 0.20 mm | |
| | 2.0 | Primary Flat Orientation | {110}+/-1 degree | Wafer Vendor |
| | 3.0 | Primary Flat Length | 57.50 +/- 2.50 mm | Wafer Vendor |
| | 4.0 | OverallWafer Secondary Flat | None | |
| | 5.0 | Overall Thickness | 434.00 +/- 12.00 µm | ADE, 100% |
| | 6.0 | LPDs > 0.3um | <30 | Tencor Particle counter |
| | 7.0 | Frontsurface condition | Polished, roughness <5A | Guaranteed by process |
| | 8.0 | Total Thickness Variation (TTV) | <5.00µm | Guaranteed by Process |
| | 9.0 | Bow | <60.00µm | ADE to ASTM F534, 100% |
| | 10.0 | Warp | <60.00µm | ADE to ASTM F534, 100% |
| | 11.0 | Edge Chips | 0 | Bright Light, 100% |
| | 12.0 | Edge Exclusion | 5mm | |
| HandleSilicon | 17.0 | Handle Growth Method | CZ | Wafer Vendor |
| | 18.0 | Handle Orientation | {100} +/- 0.5 degree | Wafer Vendor |
| | 19.0 | Handle Thickness | 400.00 +/- 10.00 µm | ADE, 100% |
| | 20.0 | Handle Doping Type | N | Wafer Vendor |
| | 21.0 | Handle Dopant | phosphorus | Wafer Vendor |
| | 22.0 | Handle Resistivity | 3 ~ 5 Ohm-cm | Wafer Vendor |
| | 23.0 | Backside Finish | Polished with lasermark and oxide | Wafer Vendor |
| BuriedOxide | 24.0 | Oxide Type | Thermal | |
| | 25.0 | Oxide Thickness | 40,000.00 +/- 2,000.00 A | Nanospec centre point, 4% |
| | 26.0 | Oxide formed on | Handle or/and Device | |
| DeviceSilicon | 27.0 | Device Growth Method | CZ | Wafer Vendor |
| | 28.0 | Device Orientation | {100} +/- 0.5 degree | Wafer Vendor |
| | 29.0 | Nominal Thickness | 30.00 +/- 0.50 µm | FTIR, 9pts, 100% |
| | 30.0 | Distance to device silicon edge from wafer edge | <= 2mm | Typical by Process |
| | 31.0 | Device Doping Type | N | Wafer Vendor |
| | 32.0 | Device Dopant | phosphorus | Wafer Vendor |
| | 33.0 | Device Resistivity | <=0.005 Ohmcm | Wafer Vendor |
| | 34.0 | Voids | none | Bright Light, 100% (note 2) |
| | 35.0 | Scratches | 0 | Bright Light, 100% (note 2) |
| | 36.0 | Haze | none | Bright Light, 100% (note 2) |

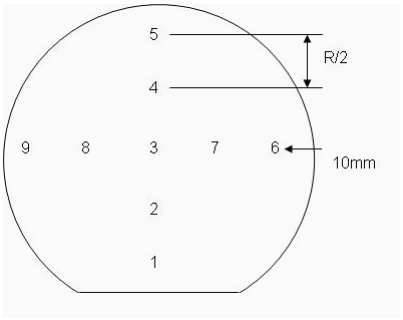
| Part Number | Customer |
|---|---|

| Category | Parameter | Specification | Measurement Method |
|---|---|---|---|
| Shipping Details | Wafer per box : | Max 25 | |
| | Packaging : | Taped Polypropylene Wafer Box<br>Empak, Ultrapak, 150.00mm<br>Antistatic Double Bagging | |
| | Lot Shipment Data | Device Thickness<br>Bow / Warp Data<br>Handle and SOI Thickness | |
| Explanatory Notes | 1. Microscope inspection performed using microscope scan as below. 5x objective. | | |



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:




Additional Information